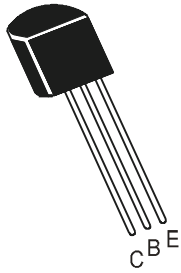


PNP SILICON PLANAR EPITAXIAL TRANSISTORS



BC 307, A, B, C
BC 308, A, B, C
BC 309, A, B, C

TO-92
Plastic Package

General Purpose Transistors Deisgned For Small Signal Amplification

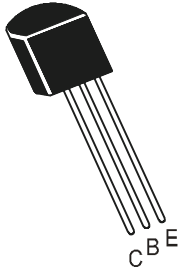
From DC To Low Radio Frequencies

ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	BC307	BC308	BC309	UNITS
Collector Emitter Voltage	V_{CEO}	45	25	25	V
Collector Base Voltage	V_{CBO}	50	30	30	V
Emitter Base Voltage	V_{EBO}	5	5	5	V
Collector Current Continuous	I_C		100		mA
Power Dissipation@ Ta=25°C	P_D		350		mW
Derate Above 25°C			2.8		mW/°C
Power Dissipation@ Tc=25°C	P_D		1		W
Derate Above 25°C			8		mW/°C
Operating And Storage Junction Temperature Range	T_j, T_{stg}	-55 to +150			°C
THERMAL RESISTANCE					
Junction to ambient	$R_{th(j-a)}$		357		°C/W
Junction to case	$R_{th(j-c)}$		125		°C/W

PNP SILICON PLANAR EPITAXIAL TRANSISTORS

BC 307, A, B, C
BC 308, A, B, C
BC 309, A, B, C



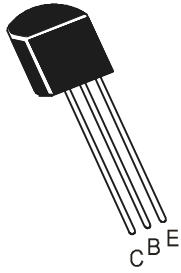
TO-92
Plastic Package

ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
Collector Emitter Breakdown Voltage	BV_{CEO}	$I_C=2mA, I_B=0$				
	BC307		45			V
	BC308, BC309		25			V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E=100\mu A, I_C=0$	5			V
Collector Emitter Leakage Current	BC307	I_{CES} $V_{CES}=50V, V_{BE}=0$			15	nA
	BC308, BC309	$V_{CES}=30V, V_{BE}=0$			15	nA
	BC307	$V_{CES}=50V, V_{BE}=0, T_A=125^\circ C$			4	μA
	BC308, BC309	$V_{CES}=30V, V_{BE}=0, T_A=125^\circ C$			4	μA
DC Current Gain	A	h_{FE} $I_C=10\mu A, V_{CE}=5V$		90		
	B			150		
	C			270		
	BC307, BC308, BC309	$I_C=2mA, V_{CE}=5V$	120		800	
	A		120	170	220	
	B		200	290	460	
	C		420	500	800	
	A	$I_C=2mA, V_{CE}=5V^*$		120		
	B			180		
	C			300		
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=0.5mA$		0.10	0.3	V
		$I_C=100mA, I_B=5mA$		0.25		V
Base Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=0.5mA$		0.7		V
		$I_C=100mA, I_B=5mA$		1.0		V
Base Emitter On Voltage	$V_{BE(on)}$	$I_C=2mA, V_{CE}=5V$	0.55	0.62	0.7	V

SILICON PLANAR EPITAXIAL TRANSISTORS

BC 307, A, B, C
 BC 308, A, B, C
 BC 309, A, B, C



TO-92
 Plastic Package

ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)

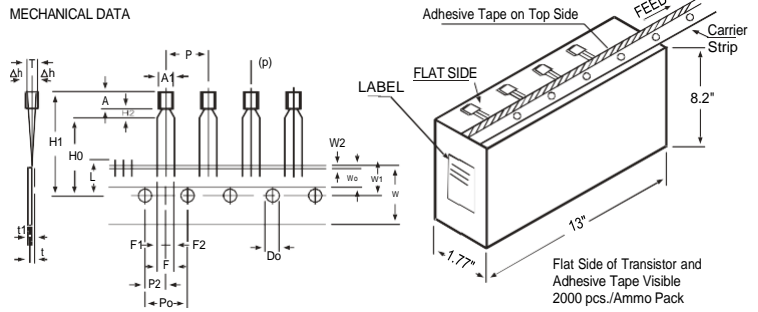
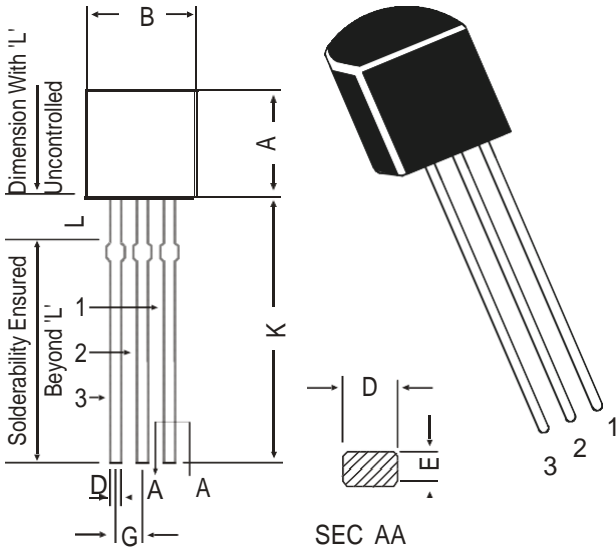
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
DYNAMIC CHARACTERISTICS						
Transition Frequency		f_T	$I_C=10mA, V_{CE}=5V$			
	BC307		$f=50MHz$	280		MHz
	BC308			320		MHz
	BC309			360		MHz
Collector Base Capacitance		C_{cbo}	$V_{CB}=10V, I_E=0$		6	pF
Noise Figure			$f=1MHz$			
	BC 309	NF	$I_C=0.2mA, V_{CE}=5V$	2	4	dB
			$R_g=2K\Omega f=30Hz$ to 15KHz			
	BC307, BC308		$f=1KHz, B=200Hz$	2	10	dB
	BC309			2	4	dB
			$R_s=2K\Omega f=30Hz$ to 15KHz			

*Pulse Condition: Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

TO-92
 Plastic Package

TO-92 Plastic Package

TO-92 Transistors on Tape and Ammo Pack



All dimensions in mm unless specified otherwise

ITEM	SYMBOL	SPECIFICATION			REMARKS
		MIN.	NOM.	MAX. TOL.	
BODY WIDTH	A1	4.0		4.8	
BODY HEIGHT	A	4.8		5.2	
BODY THICKNESS	T	3.9		4.2	
PITCH OF COMPONENT	P		12.7		±1
FEED HOLE PITCH	Po		12.7		±0.3
FEED HOLE CENTRE TO COMPONENT CENTRE	P2		6.35		±0.4
DISTANCE BETWEEN OUTER LEADS	F		5.08		+0.6 -0.2
COMPONENT ALIGNMENT	Δh		0	1	AT TOP OF BODY
TAPE WIDTH	W		18		±0.5
HOLD-DOWN TAPE WIDTH	Wo		6		±0.2
HOLE POSITION	W1		9		+0.7 -0.5
HOLD-DOWN TAPE POSITION	W2		0.5		±0.2
LEAD WIRE CLINCH HEIGHT	Ho		16		±0.5
COMPONENT HEIGHT	H1			23.25	
LENGTH OF SNIPPED LEADS	L			11.0	
FEED HOLE DIAMETER	Do		4		±0.2
TOTAL TAPE THICKNESS	t			1.2	11 0.3 - 0.6
LEAD - TO - LEAD DISTANCE F1,	F2		2.54		+0.4 -0.1
CLINCH HEIGHT	H2			3	
PULL - OUT FORCE	(P)		6N		

NOTES

1. MAXIMUM ALIGNMENT DEVIATION BETWEEN LEADS NOT TO BE GREATER THAN 0.2 mm.
2. MAXIMUM NON-CUMULATIVE VARIATION BETWEEN TAPE FEED HOLES SHALL NOT EXCEED 1 mm IN 20 PITCHES.
3. HOLDDOWN TAPE NOT TO EXCEED BEYOND THE EDGE(S) OF CARRIER TAPE AND THERE SHALL BE NO EXPOSURE OF ADHESIVE.
4. NO MORE THAN 3 CONSECUTIVE MISSING COMPONENTS ARE PERMITTED.
5. A TAPE TRAILER, HAVING AT LEAST THREE FEED HOLES ARE REQUIRED AFTER THE LAST COMPONENT.
6. SPLICES SHALL NOT INTERFERE WITH THE SPROCKET FEED HOLES.

DIM	MIN.	MAX.
A	4.32	5.33
B	4.45	5.20
C	3.18	4.19
D	0.41	0.55
E	0.35	0.50
F	5 DEG	
G	1.14	1.40
H	1.14	1.53
K	12.70	—
L	1.982	2.082

All dimensions in mm.

PIN CONFIGURATION

1. EMITTER
2. BASE
3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-92 Bulk	1K/polybag	200 gm/1K pcs	3" x 7.5" x 7.5"	5K	17" x 15" x 13.5"	80K	23 kgs
TO-92 T&A	2K/ammo box	645 gm/2K pcs	12.5" x 8" x 1.8"	2K	17" x 15" x 13.5"	32K	12.5 kgs

Disclaimer

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